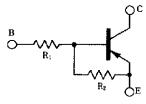


# COMPOUND TRANSISTOR

## on-chip resistor PNP silicon epitaxial transistor For mid-speed switching

#### FEATURES

On-chip bias resistor
 (R<sub>1</sub> = 4.7 kΩ, R<sub>2</sub> = 10 kΩ)



#### Symbol Parameter Unit Ratings v Collector to base voltage Vсво -60 Collector to emitter voltage -50 v VCEO Emitter to base voltage Vево -5 ٧ Collector current (DC) -100 C(DC) mΑ -200 Collector current (Pulse) IC(pulse) \* mΑ Ρт 250 Total power dissipation mW Tj °C Junction temperature 150 °C -55 to +150 Storage temperature Tstg

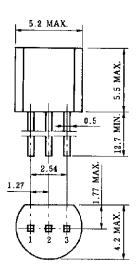
#### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Complementary transistor with AA1L3N

\* PW  $\leq$  10 ms, duty cycle  $\leq$  50 %

### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

#### PACKAGE DRAWING (UNIT: mm)



Electrode Connection

1. Emitter EIAJ : SC -43B

2. Collector JEDEC: TO-92

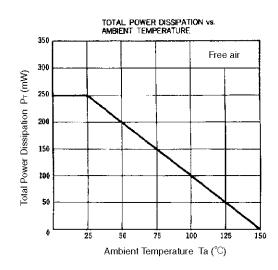
3. Base IEC : PA33

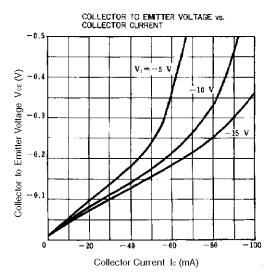
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	$V_{CB} = -50 \text{ V}, \text{ Ie} = 0$			-100	nA
DC current gain	hfe1 **	$V_{\text{CE}}$ = $-5.0$ V, Ic = $-5.0$ mA	35	60	100	-
DC current gain	hfe2 **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -50 \text{ mA}$	80	200		-
Collector saturation voltage	VCE(sat) **	$I_{C} = -5.0 \text{ mA}, I_{B} = -0.25 \text{ mA}$		-0.04	-0.2	V
Low level input voltage	VIL **	$V_{CE} = -5.0 \text{ V}, \text{ Ic} = -100 \ \mu\text{A}$		-0.9	-0.6	V
High level input voltage	VIH **	$V_{CE} = -0.2 \text{ V}, \text{ Ic} = -5.0 \text{ mA}$	-3.0	-1.5		V
Input resistance	R1		3.29	4.7	6.11	kΩ
E-to-B resistance	R2		7	10	13	kΩ
Turn-on time	ton	$V_{CC} = -5 V, R_L = 1 k\Omega$			0.2	μs
Storage time	tstg	$V_{I} = -5 V$ , $PW = 2 \mu s$			5.0	μs
Turn-off time	toff	duty cycle≤2 %			6.0	μs

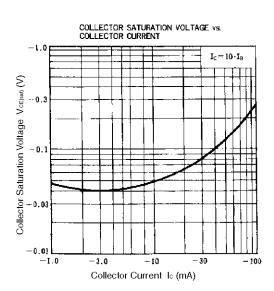
\*\* PW  $\leq$  350  $\mu$ s, duty cycle  $\leq$  2 %

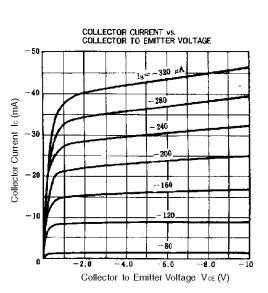
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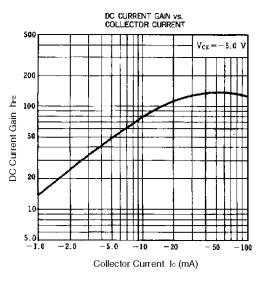
#### TYPICAL CHARACTERISTICS (Ta = 25°C)

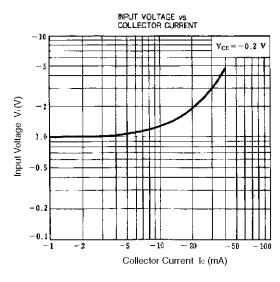




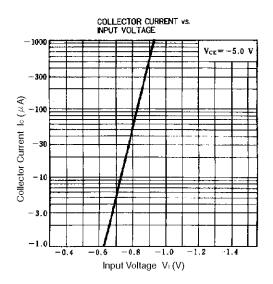


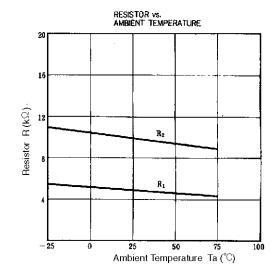






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